

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: Z&PINFN10455 Appl. No.	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Applicant JOSEF BOECK	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Filing Date January 22, 2002 Group Art Unit	

1045 U.S. PTO
10/054441
01/22/02

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
A		3,974,516	8/10/76	Steinmaier			
B		5,213,988	5/25/93	Yamauchi et al.			
C		5,747,374	5/5/98	Jeon			
D							
E							
F							
G							
H							
I							

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
RP	J	58 155 764	9/16/83	Japan			
RP	K	59 006 574	1/13/84	Japan			
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	✓	Kameyama, S. et al.: "Base Link-Up Process Technology for Self-Aligned Double Diffusion Bipolar Transistors", IEEE, 1987, pp. 27-30;
RP	✓	Nakamae, M.: "Recent Progress and Future Prospect for VLSI Si Bipolar Transistors", IEEE, 1987, pp. 5-6;

EXAMINER	<i>Ron Pompey</i>	DATE CONSIDERED
----------	-------------------	-----------------

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: Z&PINFN10455 Appl. No.	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Applicant JOSEF BOECK	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Filing Date January 22, 2002 Group Art Unit	

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	/	Chen, T et al.: "An Advanced Bipolar Transistor with Self-aligned Ion-implanted Base and W/poly Emitter", IEEE, 1987, pp. 31-33;
RP	/	Yamaguchi, T. et al.: "Process and Device Performance of a High-Speed Double Poly-Si Bipolar Technology Using Borosilicate-Poly Process with Coupling-Base Implant", IEEE, Vol. 35, No. 8, August 1988, pp. 1247-1256;

EXAMINER	for Complex	DATE CONSIDERED
5-30-03		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))			Attorney Docket No.: Z&PINFN10455 Appl. No. Applicant JOSEF BOECK Filing Date January 22, 2002 Group Art Unit																																																																																				
<table border="1"> <thead> <tr> <th>EXAMINER INITIALS</th> <th></th> <th>PATENT NO.</th> <th>DATE</th> <th>PATENTEE</th> <th>CLASS</th> <th>SUB CLASS</th> <th>FILING DATE</th> </tr> </thead> <tbody> <tr><td></td><td>A</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>B</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>C</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>D</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>E</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>F</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>G</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>H</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> <tr><td></td><td>I</td><td></td><td></td><td></td><td></td><td></td><td></td></tr> </tbody> </table>								EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE		A								B								C								D								E								F								G								H								I						
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE																																																																																
	A																																																																																						
	B																																																																																						
	C																																																																																						
	D																																																																																						
	E																																																																																						
	F																																																																																						
	G																																																																																						
	H																																																																																						
	I																																																																																						
FOREIGN PATENT DOCUMENT																																																																																							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO																																																																																
	J																																																																																						
	K																																																																																						
	L																																																																																						
	M																																																																																						
	N																																																																																						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)																																																																																							
RF	/	Sugiyama, M. et al.: "A40GHz f _T Si Bipolar Transistor LSI Technology", IEEE, 1989, pp. 9.1.1-9.1.4;																																																																																					
RF	/	Van der Velden, J. et al.: "Basic: An Advanced High-Performance Bipolar Process", IEEE, 1989, pp. 9.4.1-9.4.4;																																																																																					
EXAMINER <i>Rm Jompey</i>			DATE CONSIDERED <i>5 31-03</i>																																																																																				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.																																																																																							

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: Z&PINFN10455 Appl. No.	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Applicant JOSEF BOECK	
		Filing Date January 22, 2002 Group Art Unit	

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	✓	Shiba, T. et al.: "Base Peripheral Effects on High Performance Self-Aligned Bipolar Devices (SICOS)", Scripta Technica, Inc., 1990, pp. 100-105;
RP	✓	Hayden, J. D. et al.: "A New Technique for Forming a Shallow Link Base in a Double Polysilicon Bipolar Transistor", IEEE, 1994, pp. 63-68;

EXAMINER	RON POMPEY	DATE CONSIDERED
----------	------------	-----------------

5-30-03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: Z&PINFN10455 Appl. No.	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Applicant JOSEF BOECK	
		Filing Date January 22, 2002 Group Art Unit	

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

RP	/	Park, J. et al.: "Ultrashallow p ⁺ /n Junction Formation by 0.5-1 keV Ion Implantation", Japanese Journal of Applied Physics, Vol. 37, No. 11B, 1998, pp. L1376-L1378

EXAMINER	Rm Pompey	DATE CONSIDERED
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		